

Abstract

N-doped silicon-based solar cell

- 5 A photovoltaic device comprises a first semiconducting area (2) having an N-doped silicon base and a second semiconducting area (3) having a P-doped silicon base. The two semiconducting areas are configured to form a PN junction. The first semiconducting area (2) is devoid of boron and comprises a concentration of P-type doping impurities that is at least equal to
- 10 20% of the concentration of N-type doping impurities.

(Figure 1)